

## N-channel 40 V, 2.1 mΩ typ., 120 A STripFET™ F7 Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data

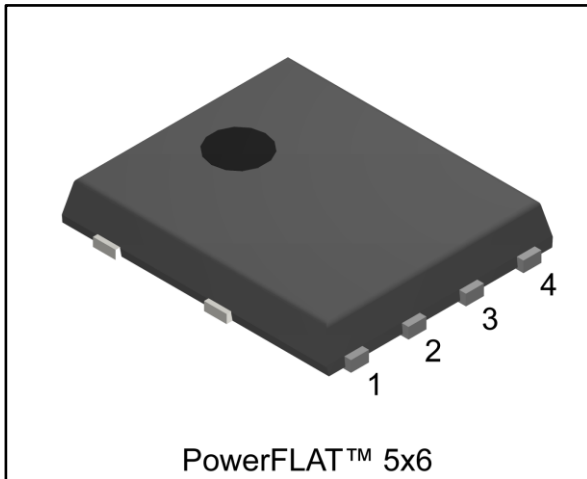
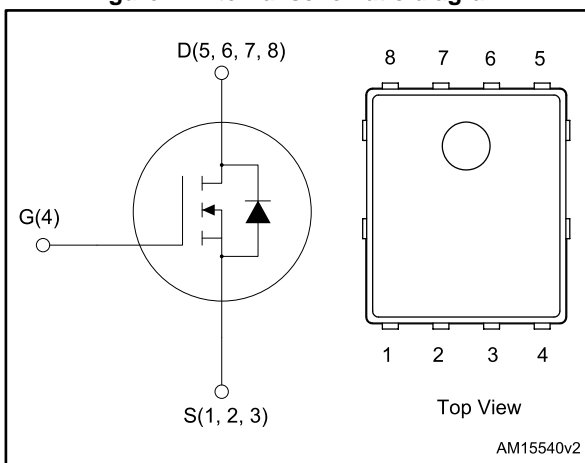


Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STL160N4F7	40 V	2.5 mΩ	120 A

- Among the lowest R<sub>DS(on)</sub> on the market
- Excellent FoM (figure of merit)
- Low C<sub>rss</sub>/C<sub>iss</sub> ratio for EMI immunity
- High avalanche ruggedness

### Applications

- Switching applications

### Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Table 1: Device summary

Order code	Marking	Package	Packing
STL160N4F7	160N4F7	PowerFLAT™ 5x6	Tape and reel

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	40	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)(2)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	120	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	108	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	480	A
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	111	W
$I_D^{(4)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	32	A
$I_D^{(4)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	22	A
$I_{DM}^{(3)(4)}$	Drain current (pulsed)	128	A
$P_{TOT}^{(4)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4.8	W
$I_{AV}$	Avalanche current	16	A
$E_{AS}$	Single pulse avalanche energy ( $T_j = 25\text{ }^\circ\text{C}$ , $I_D = 16\text{A}$ , $V_{DD} = 25\text{V}$ )	260	mJ
$T_{stg}$	Storage temperature range	-55 to 175	$^\circ\text{C}$
$T_j$	Operating junction temperature range		

**Notes:**

- <sup>(1)</sup> Drain current is limited by package
- <sup>(2)</sup> This value is rated according to  $R_{thj-c}$
- <sup>(3)</sup> Pulse width limited by safe operating area
- <sup>(4)</sup> This value is rated according to  $R_{thj-pcb}$

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max.	31.3	$^\circ\text{C}/\text{W}$
$R_{thj-case}$	Thermal resistance junction-case max.	1.35	$^\circ\text{C}/\text{W}$

**Notes:**

- <sup>(1)</sup> When mounted on FR-4 board of 1 inch<sup>2</sup>, 2oz Cu,  $t < 10\text{ sec}$

## 2 Electrical characteristics

( $T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified)

Table 4: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	40		V	V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ $V_{DS} = 40\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 16\text{ A}$		2.1	2.5	m $\Omega$

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	2300	-	pF
$C_{oss}$	Output capacitance		-	786	-	pF
$C_{rss}$	Reverse transfer capacitance		-	43	-	pF
$Q_g$	Total gate charge	$V_{DD} = 20\text{ V}$ , $I_D = 32\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 14: "Test circuit for gate charge behavior"</a> )	-	29	-	nC
$Q_{gs}$	Gate-source charge		-	13	-	nC
$Q_{gd}$	Gate-drain charge		-	5.6	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 20\text{ V}$ , $I_D = 16\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 13: "Test circuit for resistive load switching times"</a> and <a href="#">Figure 18: "Switching time waveform"</a> )	-	14	-	ns
$t_r$	Rise time		-	6.6	-	ns
$t_{d(off)}$	Turn-off delay time		-	19	-	ns
$t_f$	Fall time		-	5.7	-	ns

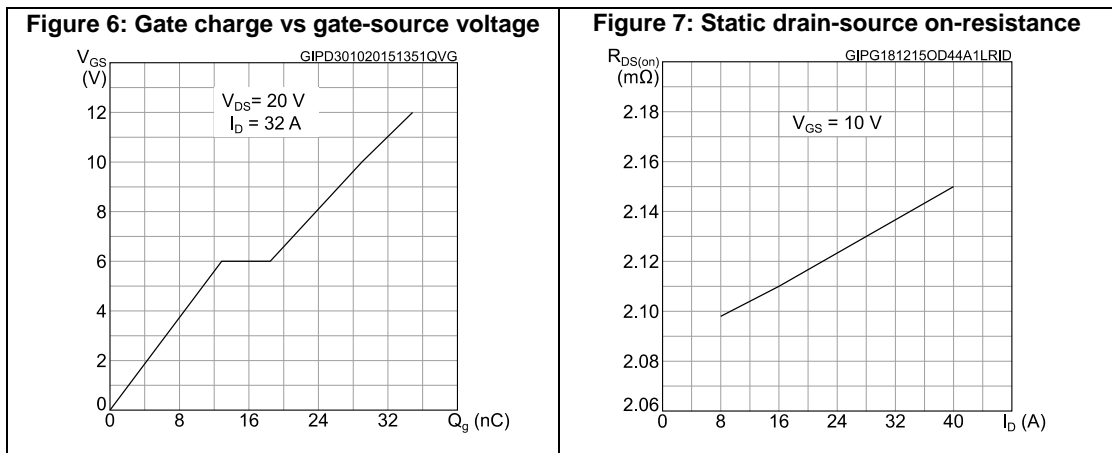
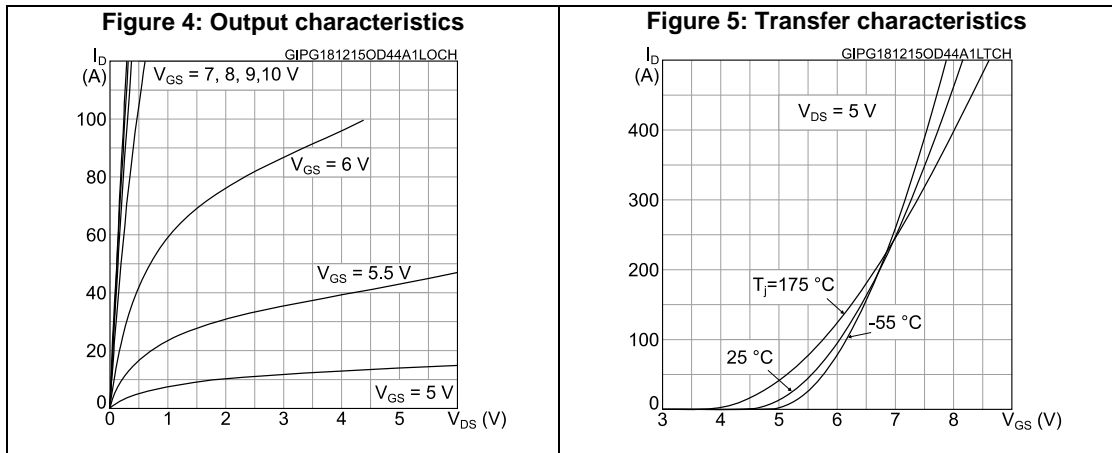
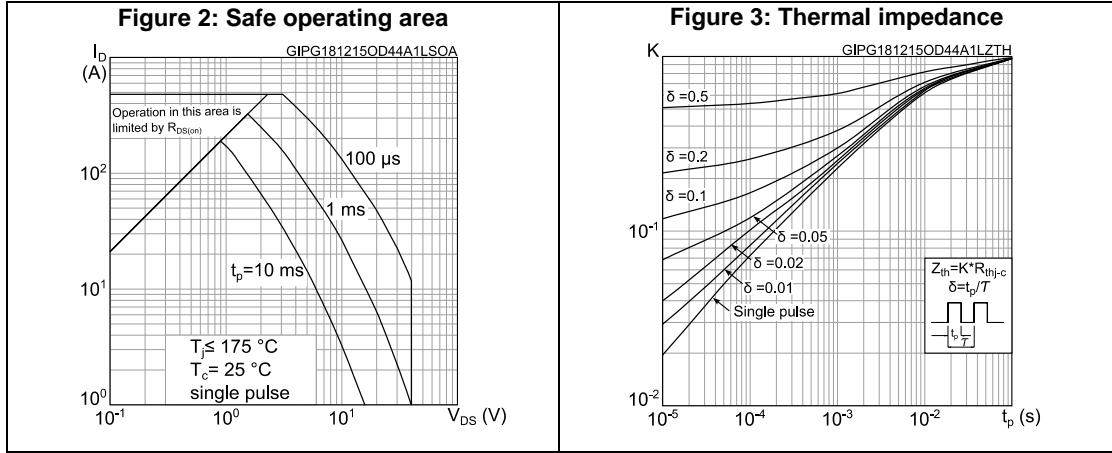
Table 7: Source-drain diode

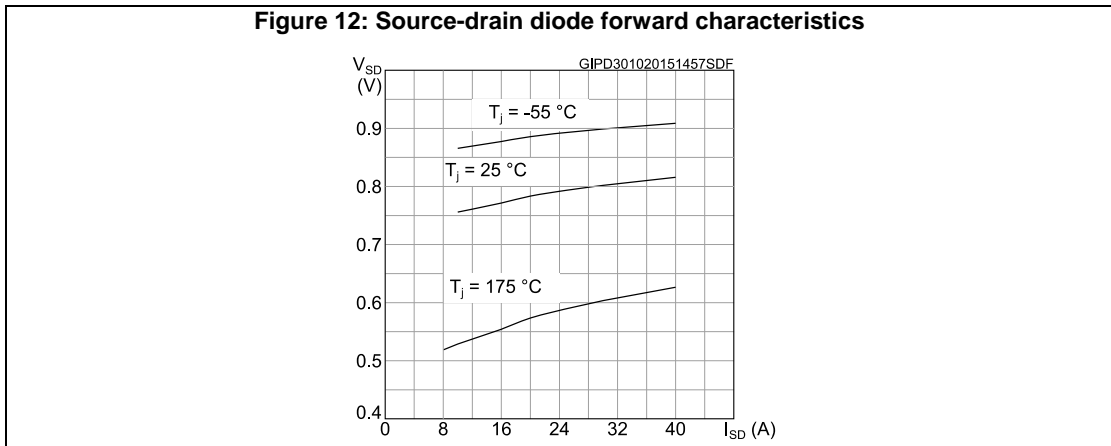
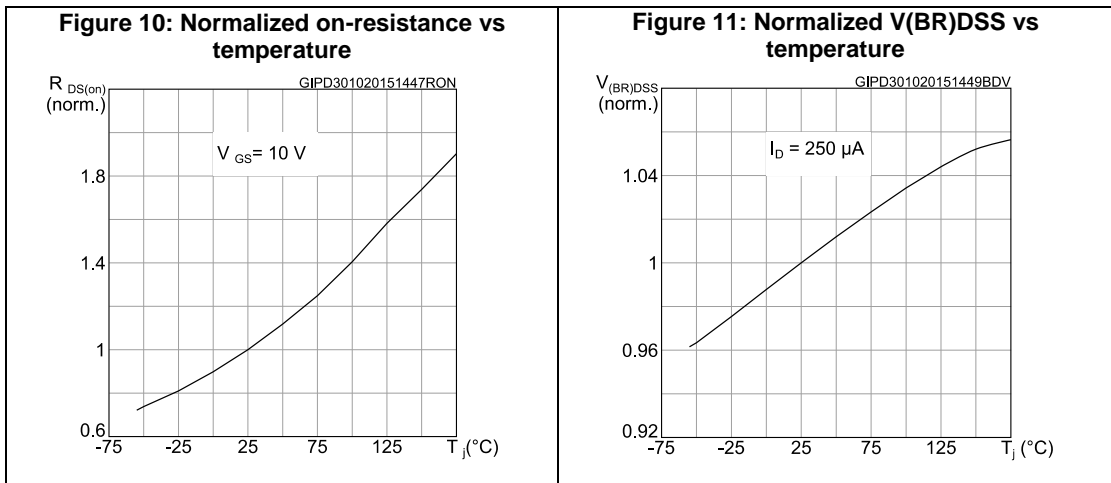
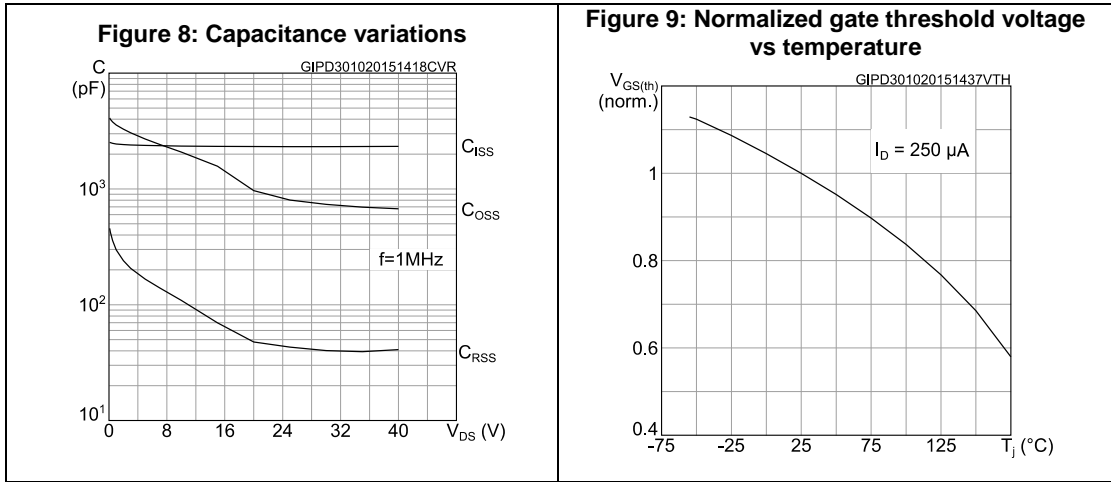
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 32 \text{ A}$ , $V_{GS} = 0 \text{ V}$	-		1.2	V
$t_{rr}$	Reverse recovery time	$I_D = 32 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 32 \text{ V}$ (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	55		ns
$Q_{rr}$	Reverse recovery charge		-	67		nC
$I_{RRM}$	Reverse recovery current		-	2.4		A

**Notes:**

<sup>(1)</sup>Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

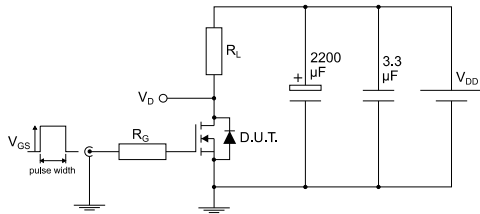
### 3 Electrical curves





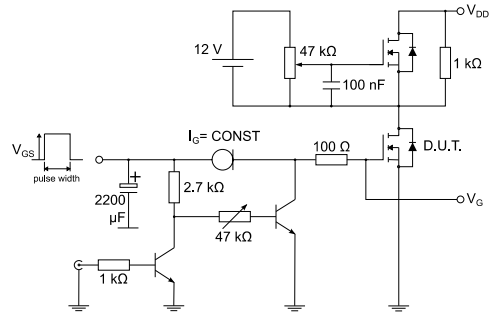
# 4 Test circuits

**Figure 13: Test circuit for resistive load switching times**



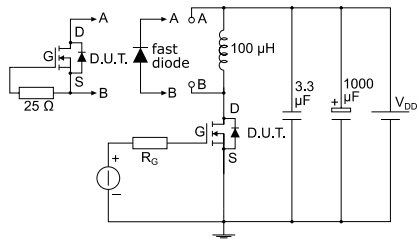
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**Figure 14: Test circuit for gate charge behavior**



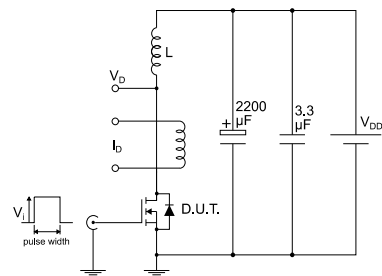
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**Figure 15: Test circuit for inductive load switching and diode recovery times**



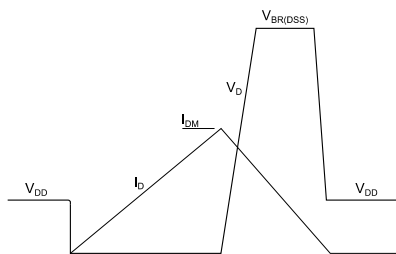
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**Figure 16: Unclamped inductive load test circuit**



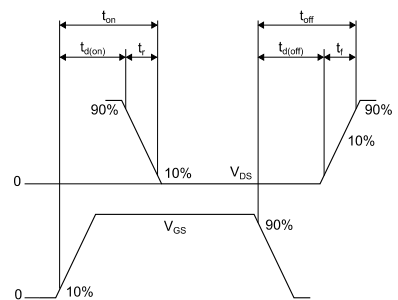
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**Figure 17: Unclamped inductive waveform**



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**Figure 18: Switching time waveform**



AM01473v1



## 5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 5.1 PowerFLAT™ 5x6 type C package information

Figure 19: PowerFLAT™ 5x6 type C package outline

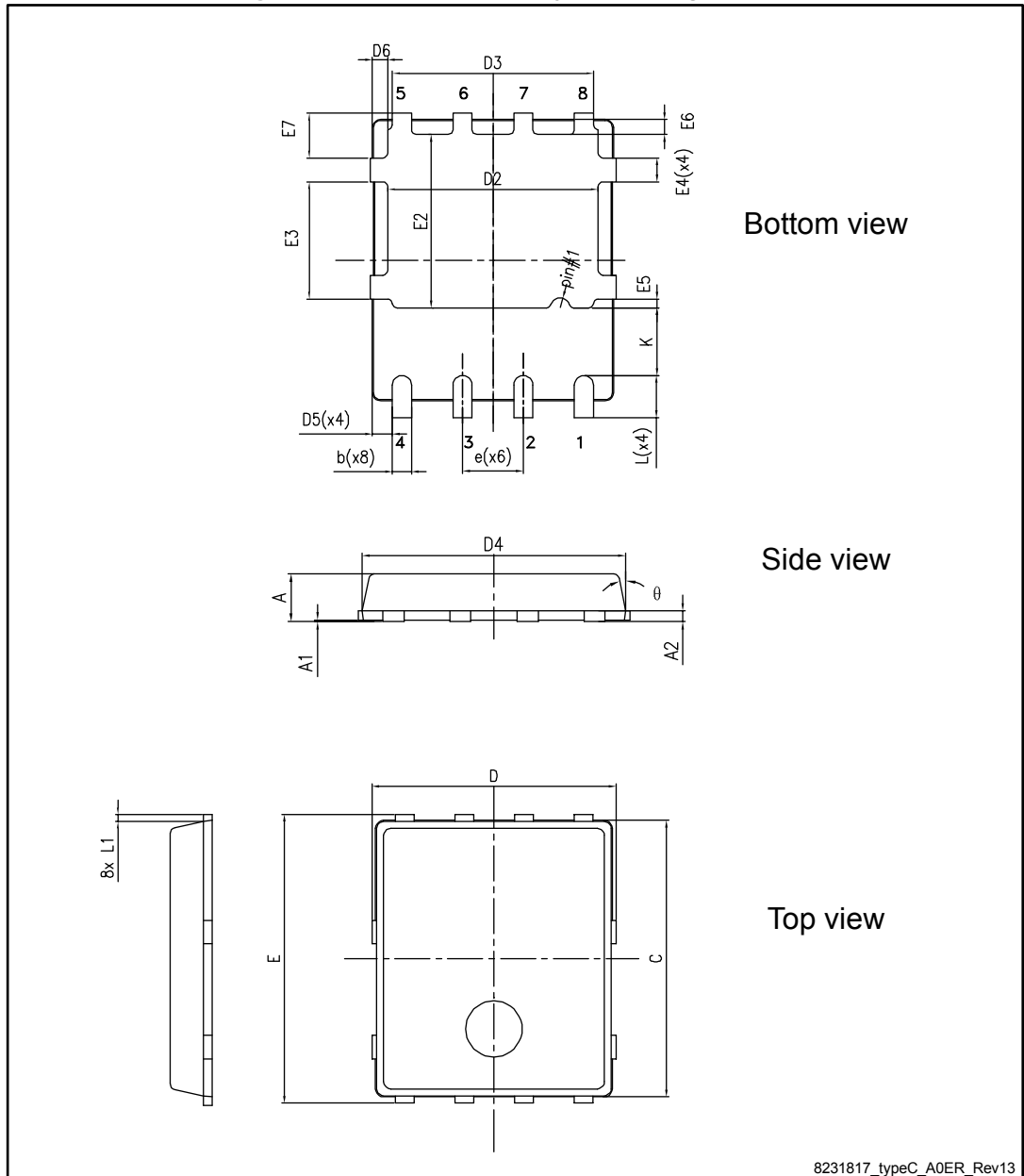
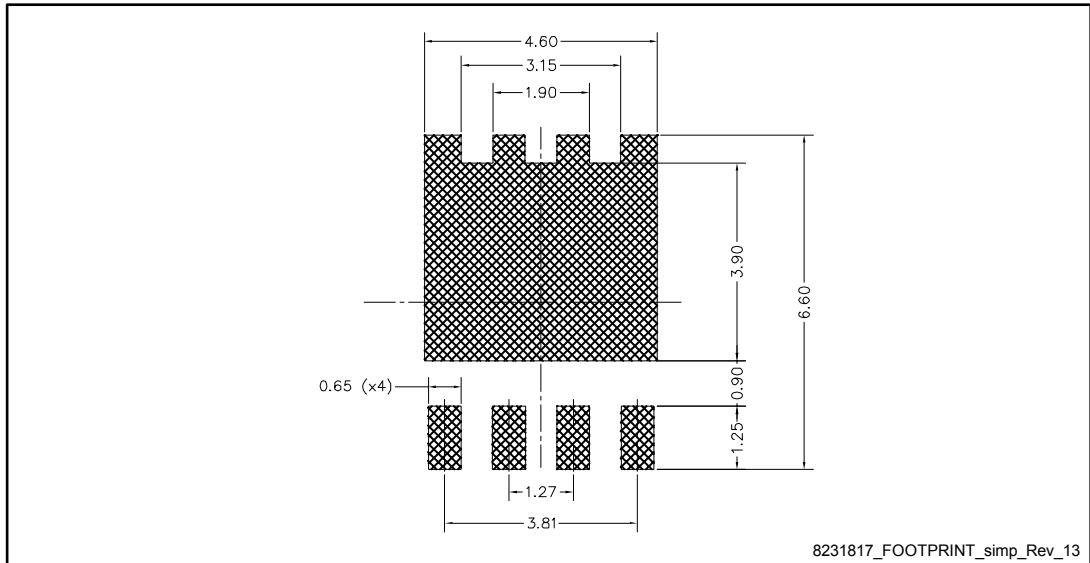


Table 8: PowerFLAT™ 5x6 type C package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.20
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.20
D5	0.25	0.40	0.55
D6	0.15	0.30	0.45
e		1.27	
E	5.95	6.15	6.35
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.450
E7	0.75	0.90	1.05
K	1.05		1.35
L	0.715		1.015
L1	0.05	0.15	0.25
θ	0°		12°

Figure 20: PowerFLAT™ 5x6 recommended footprint (dimensions are in mm)



## 5.2 PowerFLAT™ 5x6 packing information

Figure 21: PowerFLAT™ 5x6 tape (dimensions are in mm)

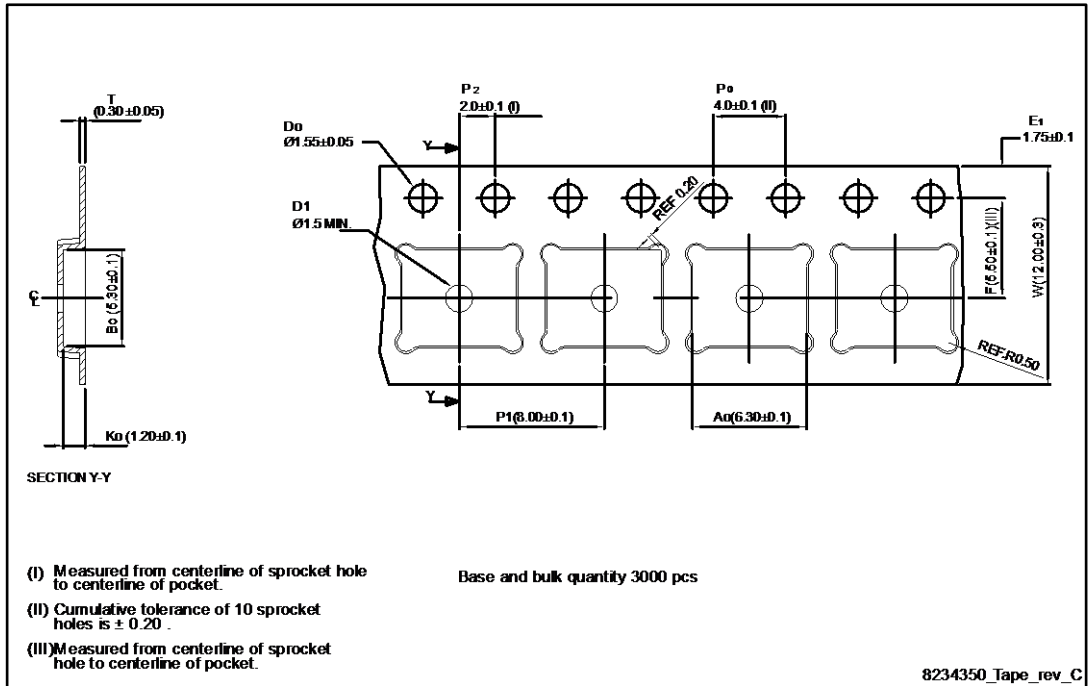


Figure 22: PowerFLAT™ 5x6 package orientation in carrier tape

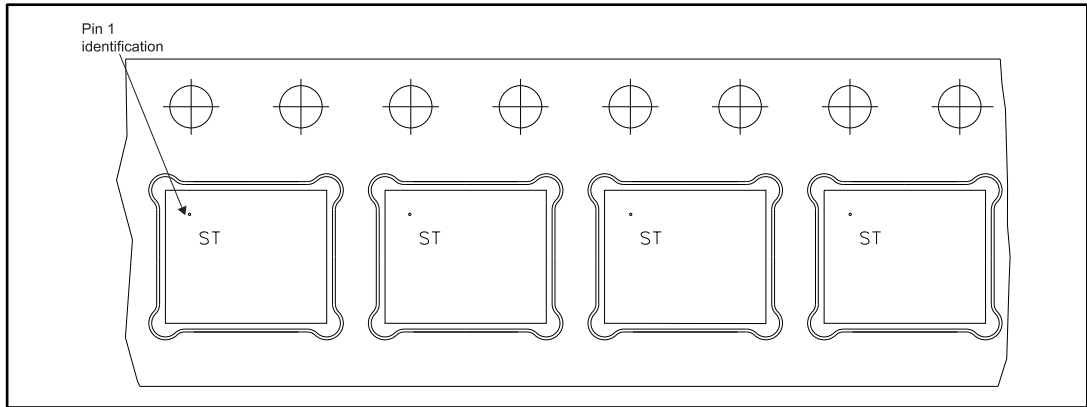
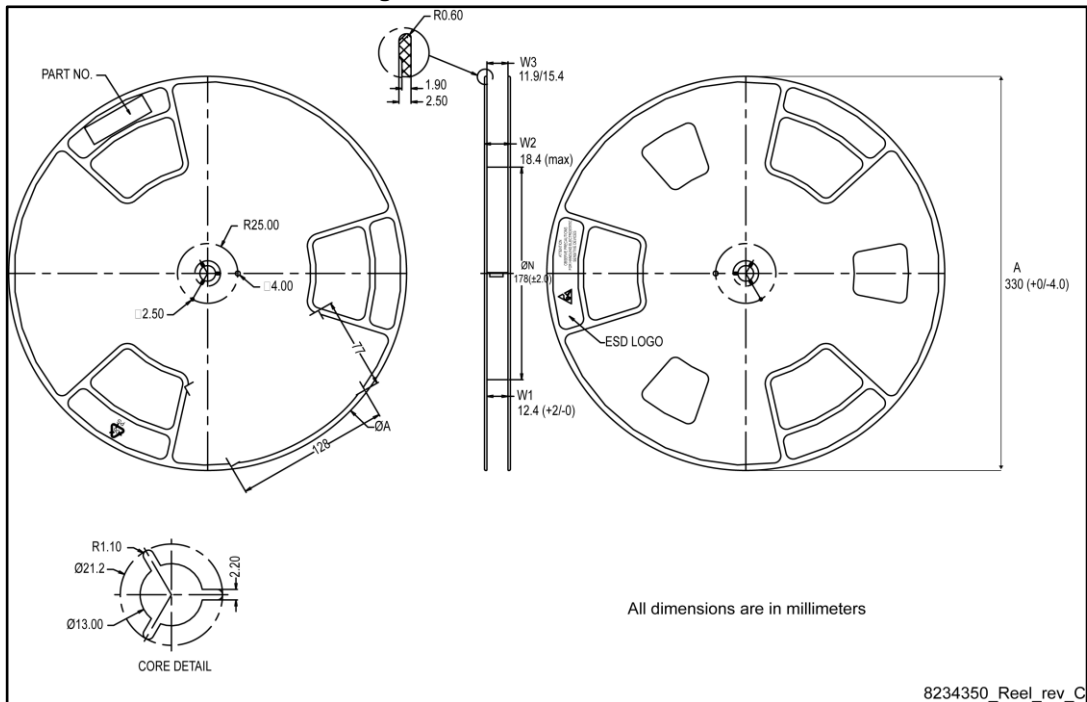


Figure 23: PowerFLAT™ 5x6 reel



## 6 Revision history

**Table 9: Document revision history**

Date	Revision	Changes
14-May-2015	1	First release.
23-Feb-2016	2	Updated title. Updated <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 4: "On /off states"</i> , <i>Table 5: "Dynamic"</i> , <i>Table 6: "Switching times"</i> and <i>Table 7: "Source-drain diode"</i> Minor text changes.

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